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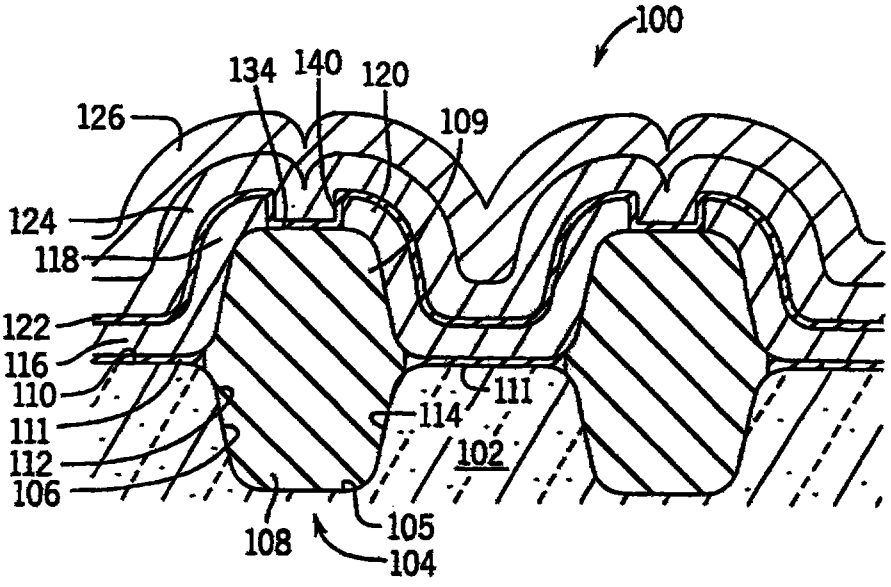
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(54) Title: NONVOLATILE MEMORY HAVING HIGH GATE COUPLING CAPACITANCE



(57) Abstract: The present invention is directed to an integrated circuit (100) having an increased gate coupling capacitance. The integrated circuit (100) includes a substrate (102) having a surface (110), the substrate (102) having a trench (106) extending below the surface (110). A trench fill material (108) is disposed in the trench (106) and has a portion (109) extending above the surface (110). A first conductive layer (116) is adjacent the trench fill material (108) and has a portion (118) extending over the portion (109) of the trench fill material (108). An insulative layer (122) is above the first conductive layer (116) and a second conductive layer (124) is adjacent the insulative material (122).

WO 01/17023 A1